

SAMTM Data Sheet SAM-1040-40-10ps-x, λ = 1040 nm

Laser wavelength λ = 1040 nm High reflection band λ = 1000 .. 1100 nm

Absorptance $A_0 = 40 \%$, resonant

Modulation depth $\Delta R = 20 \%$ Non-saturable loss $A_{ns} = 20 \%$

Saturation fluence $\Phi_{sat} = 40 \mu J/cm^2$

Relaxation time constant $\tau \sim 10 \text{ ps}$

Damage threshold $\Phi = 1 \text{ mJ/cm}^2$

Chip area 4.0 mm x 4.0 mm; other dimensions on request

Chip thickness 450 µm

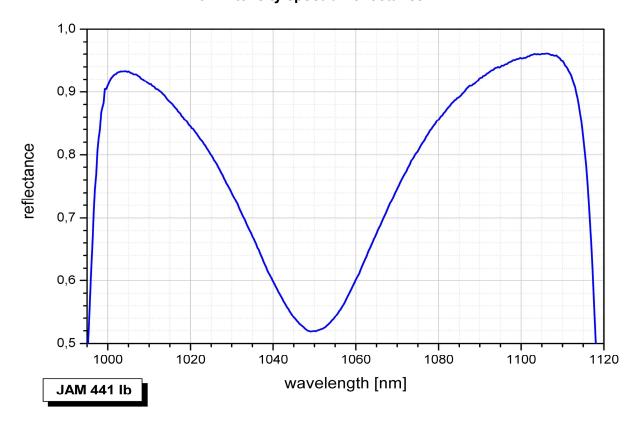
Protection the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

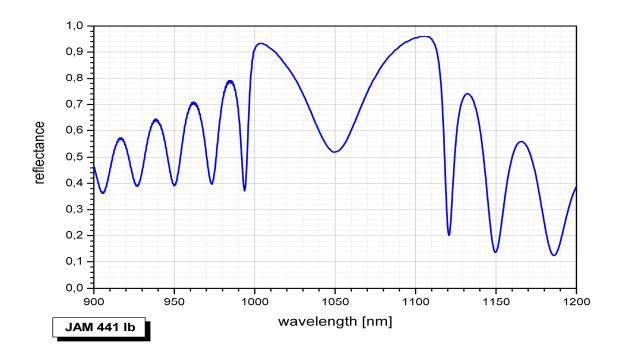
x = 0 unmounted

 $x = 12.7 \, \mathrm{g}$ glued on a gold plated Cu-cylinder with 12.7 mm \varnothing $x = 25.4 \, \mathrm{g}$ glued on a gold plated Cu-cylinder with 25.4 mm \varnothing $x = 12.7 \, \mathrm{s}$ soldered on a gold plated Cu-cylinder with 12.7 mm \varnothing $x = 25.4 \, \mathrm{s}$ soldered on a gold plated Cu-cylinder with 25.4 mm \varnothing x = FCmounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance







Saturation measurement of a SAM-1064-25 from the same wafer

